

Features

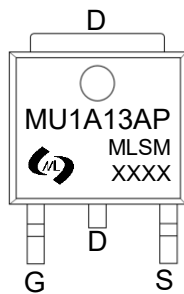
- High density cell design for ultra low $R_{DS(ON)}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high EAS

Product Summary

V_{DS}	$R_{DS(ON)}$ TYP	I_D
-100V	155mΩ@-10V	-13A
	170mΩ@-4.5V	

Application

- Power management
- Portable equipment

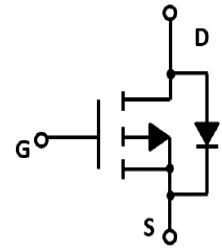


MU1A13AP: Device code
XXXX: Code

Marking and pin assignment



TO-252 top view



Schematic diagram



Pb-Free



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)			
V_{DS}	Drain-Source Breakdown Voltage	-100	V
V_{GS}	Gate-Source Voltage	±20	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-50 to 155	°C
I_S	Diode Continuous Forward Current	Tc=25°C -13	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	Tc=25°C -40	A
I_D	Continuous Drain Current	Tc=25°C -13	A
P_D	Maximum Power Dissipation	Tc=25°C 63	W
E_{AS}	Single Pulsed Avalanche Energy ^{Note1}	7.5	mJ

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MU1A13AP	TO-252	MU1A13AP	2,500	5,000	35,000	13"reel

Electrical Characteristics (T _J =25°C unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T _J = 25°C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-100	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-100V, V _{GS} =0V	--	--	-1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1.0	-1.5	-3.0	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =-10V, I _D =-8A	--	155	200	mΩ
		V _{GS} =-4.5V, I _D =-6A	--	170	250	mΩ
Dynamic Electrical Characteristics @ T _J = 25°C (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =-50V, V _{GS} =0V, f=1MHz	--	1488	--	pF
C _{OSS}	Output Capacitance		--	39	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	30	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =-50V, I _D =-6A, V _{GS} =-10V	--	26.5	--	nC
Q _{gs}	Gate Source Charge		--	6	--	nC
Q _{gd}	Gate Drain Charge		--	4	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =-50V, I _D =-6A, V _{GS} =-10V, R _G =4.5Ω	--	14	--	nS
t _r	Turn-on Rise Time		--	45	--	nS
t _{d(off)}	Turn-Off Delay Time		--	227	--	nS
t _f	Turn-Off Fall Time		--	93	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	T _J =25°C, I _S =-13A	--	-0.8	-1.2	V

Note:

- 1、EAS Test condition: V_{DD}=-100V, L=0.1mH, V_{GS}=-10V, I_{AS}=-12.25A, R_G=25Ω, Starting T_J = 25°C

Typical Operating Characteristics

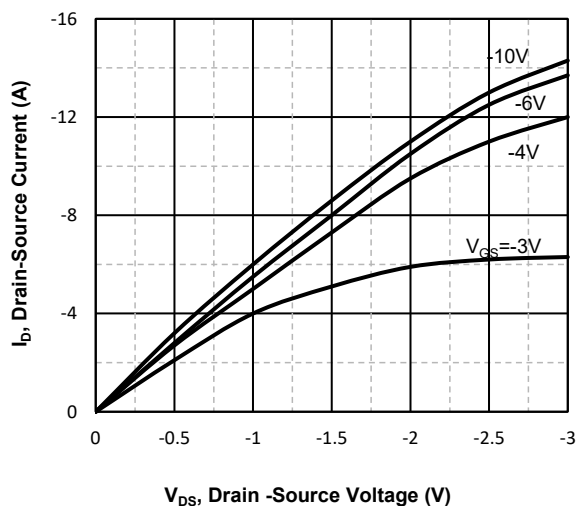


Fig1. Typical Output Characteristics

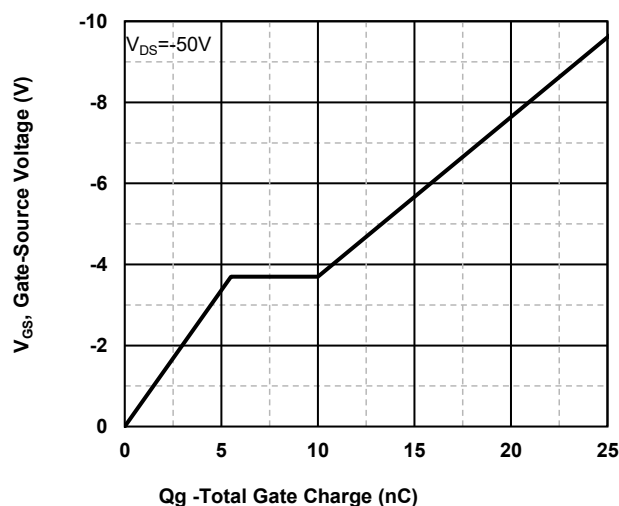


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

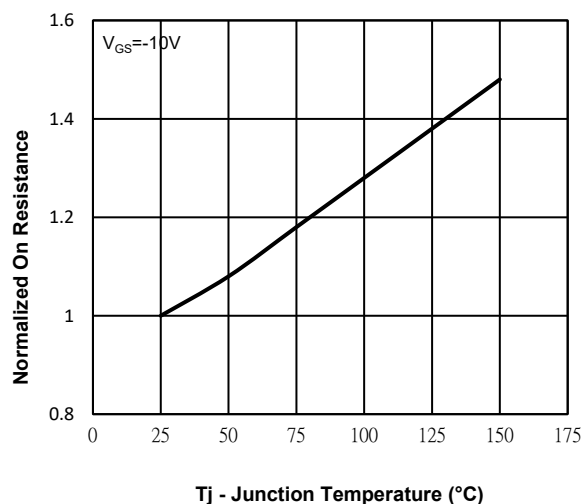


Fig3. Normalized On-Resistance Vs. Temperature

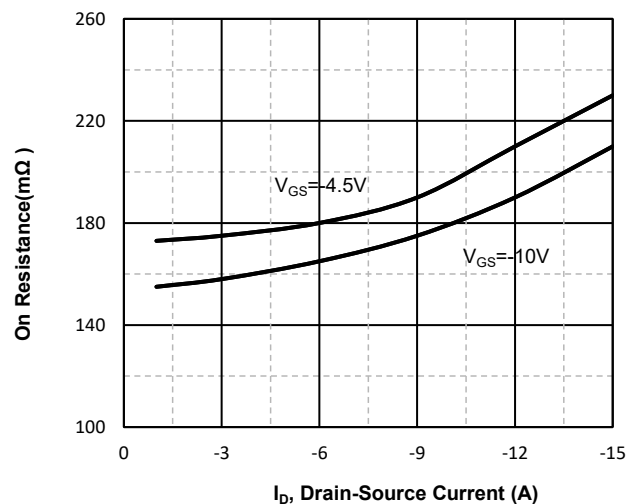


Fig4. On-Resistance Vs. Drain-Source Current

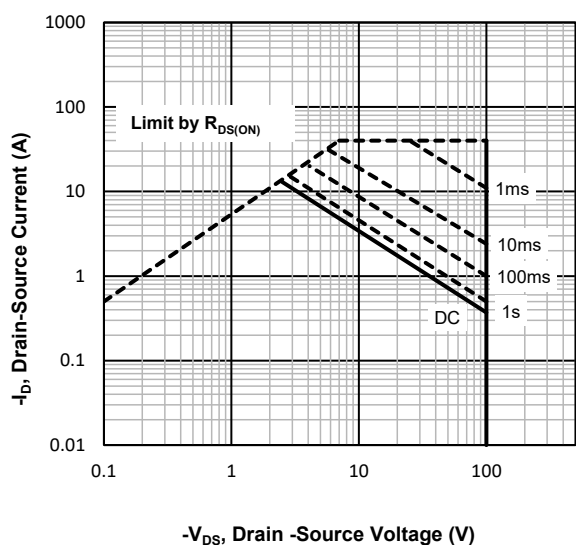


Fig5. Maximum Safe Operating Area

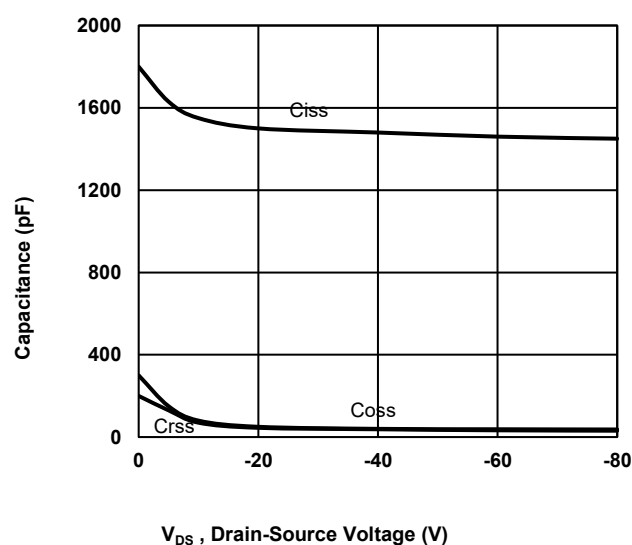
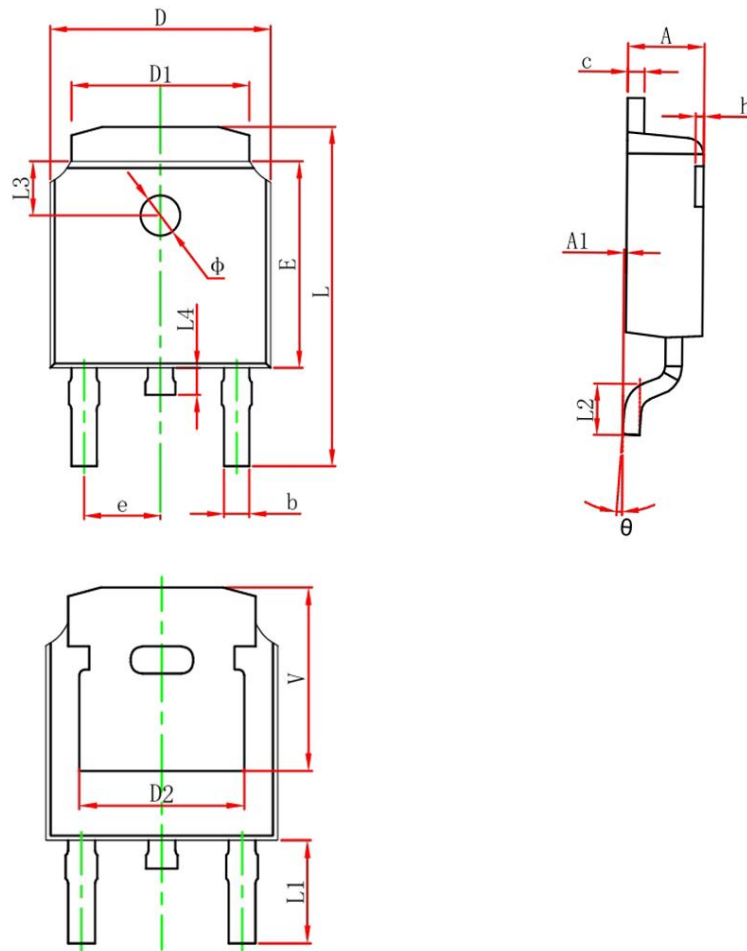


Fig6. Typical Capacitance Vs. Drain-Source Voltage

TO-252 Package information


Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.450	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.386	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	